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Diodes Incorporated MMBT5401-7

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MMBT5401

150V PNP SMALL SIGNAL TRANSISTOR IN SOT23

Features

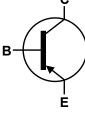
- **Epitaxial Planar Die Construction**
- Complementary NPN Type MMBT5551
- Ideal for Low Power Amplification and Switching
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

Mechanical Data

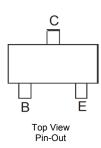
- Case: SOT23
- Case material: molded plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (Approximate)



Top View



Device Symbol



Ordering Information (Notes 4 & 5)

1					
Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT5401-7-F	AEC-Q101	K4M	7	8	3,000
MMBT5401-13-F	AEC-Q101	K4M	13	8	10,000
MMBT5401Q-7-F	Automotive	K4M	7	8	3,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. Notes:

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/. 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



K4M = Product Type Marking Code YM = Date Code Marking Y = Year (ex: N = 2002) M = Month (ex: 9 = September)

Date Code Kev

	51105																	
Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015
Code	J	K	L	М	Ν	Р	R	S	Т	U	V	W	Х	Y	Z	Α	В	С
Month	Jar		Feb	Ма	r	Apr	May		Jun	Ju		Aug	Sep		Oct	Nov	,	Dec
Month	Jai		1.60	Ivia		лрі	i i i i i i i i i i i i i i i i i i i	/	Juli	Jui		Aug	0ep		000	1101		Dec
Code	1		2	3		4	5		6	7		8	9		0	N		D





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Absolute Maximum Ratings (@T _A = +25°C, unless otherwise specified.)								
Characteristic	Symbol	Value	Unit					
Collector-Base Voltage	V _{CBO}	-160	V					
Collector-Emitter Voltage	V _{CEO}	-150	V					
Emitter-Base Voltage	V _{EBO}	-5.0	V					
Collector Current	Ι _C	-600	mA					

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 6)	Б	310	mW
	(Note 7)	P _D	350	11177
Thermal Desistance Junction to Ambient	(Note 6)	D	403	0000
Thermal Resistance, Junction to Ambient	(Note 7)	R _{θJA}	357	°C/W
Thermal Resistance, Junction to Leads (Note 8)		R _{θJL}	350	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state. 7. Same as note (6), except the device is mounted on 15 mm x 15mm 1oz copper.

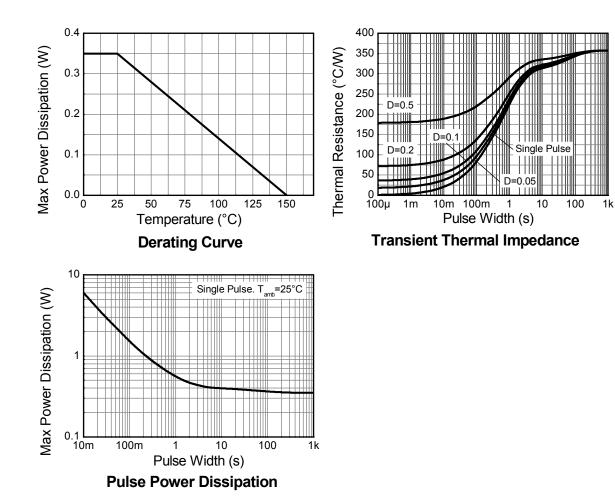
8. Thermal resistance from junction to solder-point (at the end of the leads).

9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



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Thermal Characteristics and Derating Information







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Electrical Characteristics (@T _A = +25°C, unless	s otherwise sp	pecified.)			
Characteristic	Symbol	Min	Мах	Unit	Test Condition
OFF CHARACTERISTICS (Note 10)					÷
Collector-Base Breakdown Voltage	BV _{CBO}	-160		V	$I_{\rm C}$ = -100µA, $I_{\rm E}$ = 0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-150	_	V	I _C = -1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5.0	_	V	$I_E = -10\mu A$, $I_C = 0$
Collector Cutoff Current	I _{CBO}		-50 -50	nA μA	V _{CB} = -120V, I _E = 0 V _{CB} = -120V, I _E = 0, T _A = +100°C
Emitter Cutoff Current	I _{EBO}	_	-50	nA	$V_{EB} = -4.0V, I_{C} = 0$
ON CHARACTERISTICS (Note 10)					<u> </u>
DC Current Gain	h _{FE}	50 60 50	 240 	_	I _C = -1.0mA, V _{CE} = -5.0V I _C = -10mA, V _{CE} = -5.0V I _C = -50mA, V _{CE} = -5.0V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	-0.2 -0.5	V	I _C = -10mA, I _B = -1.0mA I _C = -50mA, I _B = -5.0mA
Base-Emitter Saturation Voltage	$V_{\text{BE(SAT)}}$		-1.0	V	I_{C} = -10mA, I_{B} = -1.0mA I_{C} = -50mA, I_{B} = -5.0mA
SMALL SIGNAL CHARACTERISTICS			•		
Output Capacitance	C _{obo}		6.0	pF	V _{CB} = -10V, f = 1.0MHz, I _E = 0
Small Signal Current Gain	h _{fe}	40	200	—	V _{CE} = -10V, I _C = -1.0mA, f = 1.0kHz
Current Gain-Bandwidth Product	f _T	100	300	MHz	V _{CE} = -10V, I _C = -10mA, f = 100MHz
Noise Figure	NF	_	8.0	dB	V_{CE} = -5.0V, I _C = -200µA, R _S = 10Ω, f = 1.0kHz

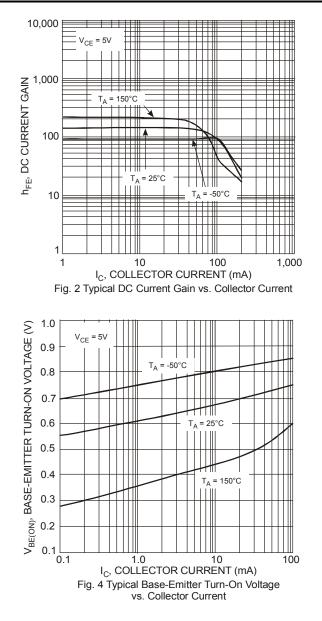
Notes: 10. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.





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Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



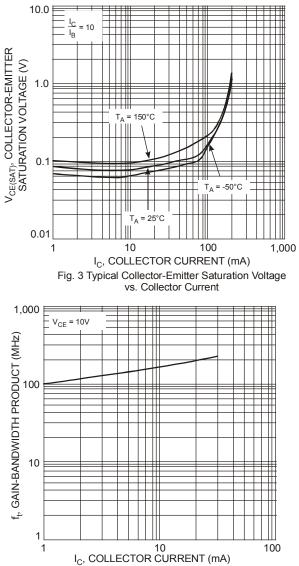


Fig. 5 Typical Gain-Bandwidth Product vs. Collector Current

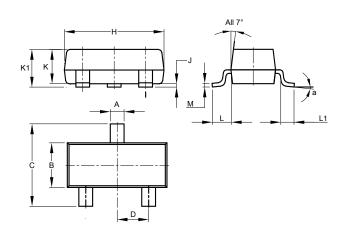




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Package Outline Dimensions

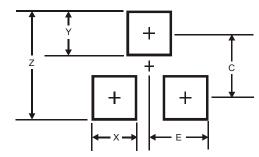
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23									
Dim	Min	Max	Тур						
Α	0.37	0.51	0.40						
В	1.20	1.40	1.30						
с	2.30	2.50	2.40						
D	0.89	1.03	0.915						
F	0.45	0.60	0.535						
G	1.78	2.05	1.83						
H	2.80	3.00	2.90						
ر	0.013	0.10	0.05						
Κ	0.890	1.00	0.975						
K1	0.903	1.10	1.025						
L	0.45	0.61	0.55						
L1	0.25	0.55	0.40						
М	0.085	0.150	0.110						
а		8°							
All	Dimens	ions in	mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.





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